

# Gang Qiu

## List of Publications by Year in descending order

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Version: 2024-02-01

38  
papers

3,594  
citations

257101

24  
h-index

525886

27  
g-index

38  
all docs

38  
docs citations

38  
times ranked

4243  
citing authors

#	ARTICLE	IF	CITATIONS
1	The resurrection of tellurium as an elemental two-dimensional semiconductor. Npj 2D Materials and Applications, 2022, 6, .	3.9	36
2	Mesoscopic Transport of Quantum Anomalous Hall Effect in the Submicron Size Regime. Physical Review Letters, 2022, 128, .	2.9	12
3	Selenene and Tellurene. , 2022, , 197-224.		2
4	Bilayer Quantum Hall States in an n-Type Wide Tellurium Quantum Well. Nano Letters, 2021, 21, 7527-7533.	4.5	6
5	High-Frequency Tellurene MOSFETs with Biased Contacts. , 2021, , .		0
6	Ultrafast photoinduced band splitting and carrier dynamics in chiral tellurium nanosheets. Nature Communications, 2020, 11, 3991.	5.8	39
7	Gate-tunable strong spin-orbit interaction in two-dimensional tellurium probed by weak antilocalization. Physical Review B, 2020, 101, .	1.1	29
8	Quantum Hall effect of Weyl fermions in n-type semiconducting tellurene. Nature Nanotechnology, 2020, 15, 585-591.	15.6	63
9	Raman response and transport properties of tellurium atomic chains encapsulated in nanotubes. Nature Electronics, 2020, 3, 141-147.	13.1	126
10	Microscopic origin of inhomogeneous transport in four-terminal tellurene devices. Applied Physics Letters, 2020, 117, .	1.5	0
11	Imaging Carrier Inhomogeneities in Ambipolar Tellurene Field Effect Transistors. Nano Letters, 2019, 19, 1289-1294.	4.5	31
12	Thermoelectric Performance of 2D Tellurium with Accumulation Contacts. Nano Letters, 2019, 19, 1955-1962.	4.5	81
13	Solar-Blind UV Photodetector Based on Atomic Layer-Deposited $\text{Cu}_2\text{O}$ and Nanomembrane $\text{In}_2\text{Ga}_2\text{O}_3$ pn Oxide Heterojunction. ACS Omega, 2019, 4, 20756-20761.	1.6	35
14	A ferroelectric semiconductor field-effect transistor. Nature Electronics, 2019, 2, 580-586.	13.1	317
15	Hybrid dual-channel phototransistor based on 1D t-Se and 2D ReS <sub>2</sub> mixed-dimensional heterostructures. Nano Research, 2019, 12, 669-674.	5.8	34
16	Data-driven and probabilistic learning of the process-structure-property relationship in solution-grown tellurene for optimized nanomanufacturing of high-performance nanoelectronics. Nano Energy, 2019, 57, 480-491.	8.2	44
17	(Invited) High-Performance 2D Tellurium Transistors Towards CMOS Logic Applications. ECS Meeting Abstracts, 2019, , .	0.0	0
18	Field-effect transistors made from solution-grown two-dimensional tellurene. Nature Electronics, 2018, 1, 228-236.	13.1	591

#	ARTICLE	IF	CITATIONS
19	Ultrafast Laser-Induced Confined Metaphase Transformation for Direct Writing of Black Phosphorus Thin Films. <i>Advanced Materials</i> , 2018, 30, 1704405.	11.1	17
20	Steep-slope hysteresis-free negative capacitance MoS <sub>2</sub> transistors. <i>Nature Nanotechnology</i> , 2018, 13, 24-28.	15.6	422
21	High-Performance Few-Layer Tellurium CMOS Devices Enabled by Atomic Layer Deposited Dielectric Doping Technique. , 2018, , .		16
22	Epitaxial Growth of 1D Atomic Chain Based Se Nanoplates on Monolayer ReS <sub>2</sub> for High-Performance Photodetectors. <i>Advanced Functional Materials</i> , 2018, 28, 1806254.	7.8	52
23	Wafer-scale Material-device Correlation of Tellurene MOSFETs. , 2018, , .		2
24	Ferroelectric Field-Effect Transistors Based on MoS <sub>2</sub> and CuInP <sub>2</sub> S <sub>6</sub> Two-Dimensional van der Waals Heterostructure. <i>ACS Nano</i> , 2018, 12, 6700-6705.	7.3	246
25	Tellurene: its physical properties, scalable nanomanufacturing, and device applications. <i>Chemical Society Reviews</i> , 2018, 47, 7203-7212.	18.7	214
26	2D Ferroelectric $\text{CuInP}_2\text{S}_6$ : Synthesis, ReRAM, and FeRAM. , 2018, , .		0
27	Quantum Transport and Band Structure Evolution under High Magnetic Field in Few-Layer Tellurene. <i>Nano Letters</i> , 2018, 18, 5760-5767.	4.5	60
28	Chemical Exfoliation of Black Phosphorus for Nanoelectronics Applications. <i>MRS Advances</i> , 2017, 2, 3697-3702.	0.5	0
29	One-Dimensional van der Waals Material Tellurium: Raman Spectroscopy under Strain and Magneto-Transport. <i>Nano Letters</i> , 2017, 17, 3965-3973.	4.5	272
30	High-Performance Depletion/Enhancement-mode $\text{Ga}_2\text{O}_3$ on Insulator (GOOI) Field-Effect Transistors With Record Drain Currents of 600/450 mA/mm. <i>IEEE Electron Device Letters</i> , 2017, 38, 103-106.	2.2	247
31	Controlled Growth of a Large-Size 2D Selenium Nanosheet and Its Electronic and Optoelectronic Applications. <i>ACS Nano</i> , 2017, 11, 10222-10229.	7.3	189
32	$\text{In}_2\text{Ga}_2\text{O}_3$ on insulator field-effect transistors with drain currents exceeding 1.5 mA/mm and their self-heating effect. <i>Applied Physics Letters</i> , 2017, 111, .	1.5	170
33	How Important Is the Metal-Semiconductor Contact for Schottky Barrier Transistors: A Case Study on Few-Layer Black Phosphorus?. <i>ACS Omega</i> , 2017, 2, 4173-4179.	1.6	24
34	Observation of Optical and Electrical In-Plane Anisotropy in High-Mobility Few-Layer ZrTe <sub>5</sub> . <i>Nano Letters</i> , 2016, 16, 7364-7369.	4.5	80
35	Few-layer black phosphorous PMOSFETs with BN/Al <sub>2</sub> O <sub>3</sub> bilayer gate dielectric: Achieving $I_{\text{on}}/I_{\text{off}}=850$ at $V_{\text{g}}=340$ V, and $R_{\text{c}}=0.58 \text{ k}\Omega$ . , 2016, , .		10
36	Al <sub>2</sub> O <sub>3</sub> / $\text{Ga}_2\text{O}_3$ (-201) Interface Improvement Through Piranha Pretreatment and Postdeposition Annealing. <i>IEEE Electron Device Letters</i> , 2016, 37, 1411-1414.	2.2	109

#	ARTICLE	IF	CITATIONS
37	Write disturb analyses on half-selected cells of cross-point RRAM arrays. , 2014, , .		18
38	Degradation Characteristics of Resistive Switching Memory Devices Correlated with Electric Field Induced Ion-Migration Effect of Anode. Chinese Physics Letters, 2013, 30, 117104.	1.3	0